

**Silicon PNP Power Transistors**

**2SB628**

**DESCRIPTION**

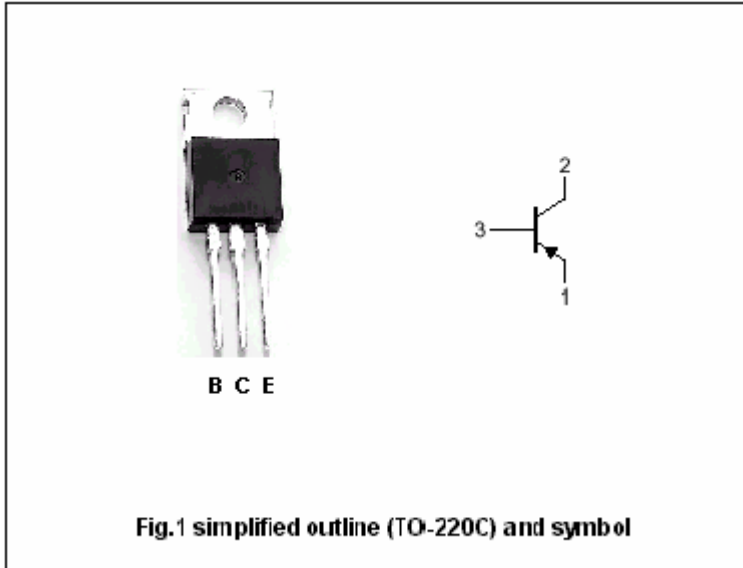
- With TO-220C package
- High  $V_{CEO}$

**APPLICATIONS**

- Low frequency power amplifier color TV vertical deflection output

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings( $T_a=25^\circ$ )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-160	V
$V_{CEO}$	Collector-emitter voltage	Open base	-160	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-1.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ$	20	W
$T_j$	Junction temperature		150	$^\circ$
$T_{stg}$	Storage temperature		-45~150	$^\circ$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-160			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-0.1mA; I <sub>E</sub> =0	-160			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-0.1mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-0.3A; I <sub>B</sub> =-30mA			-1.0	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-0.3A; V <sub>CE</sub> =-4V			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.3A; V <sub>CE</sub> =-5V	40		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.3A; V <sub>CE</sub> =-5V		40		MHz

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PACKAGE OUTLINE

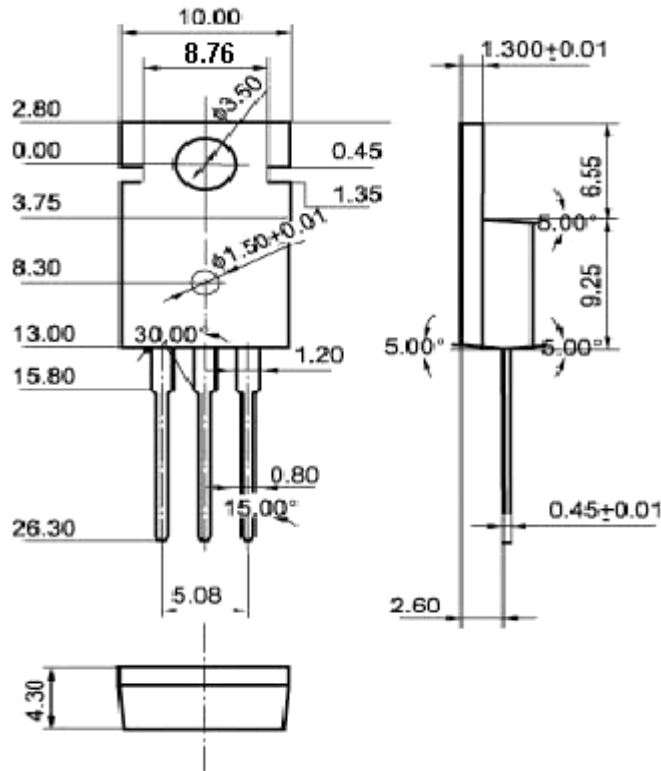


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)